

Claims

[c1]

1. A semiconductor light source for emitting light to illuminate a space used by humans, the semiconductor light source comprising:

an enclosure, said enclosure being fabricated from a material substantially transparent to white light,

a base to which said enclosure is mounted,

an interior volume within said enclosure,

a secondary heat sink located in said interior volume, said secondary heat sink being capable of drawing heat from one or more semiconductors devices,

a plurality of primary heat sinks mounted on said secondary heat sink, each of said primary heat sinks being smaller than said secondary heat sink,

a semiconductor chip capable of emitting light mounted on one of said primary heat sinks, said semiconductor chip being capable of emitting monochromatic light, said semiconductor chip being selected from the group consisting of light emitting diodes, light emitting diode arrays, laser chips, and VCSEL chips,

said chip including a substrate on which epitaxial layers are grown,

a buffer layer located on said substrate, said buffer layer serving to mitigate differences in material properties between said substrate and other epitaxial layers,

a first cladding layer serving to confine electron movement within the chip, said first cladding layer being adjacent said buffer layer,

an active layer, said active layer emitting light when electrons jump to a valance state,

a second cladding layer, said second cladding layer positioned so that said active layer lies between cladding layers, and

a contact layer on which an electron may be mounted for powering said chip, and

- [c2] a coating for converting monochromatic light emitted by said chip to white light.
- [c3] 2. A device as recited in claim 1 further comprising a first and a second reflective layers, each of said first and second reflective layers being located on opposite sides of said active layer, said reflective layers serving to reflect light emitted by said active layer.
- [c4] 3. A device as recited in claim 2 wherein said reflective layers include multiple quantum wells.
- [c5] 4. A device as recited in claim 1 wherein said substrate is selected from the group consisting of Si, GaAs, GaN, InP, sapphire, SiC, GaSb, InAs.
- [c6] 5. A device as recited in claim 1 wherein said substrate is electrically conductive.
- [c7] 6. A device as recited in claim 1 wherein said substrate is electrically insulative.
- [c8] 7. A device as recited in claim 1 wherein at least one of said epitaxial layers includes a material selected from the group consisting of GaN, AlGaN, AlN, AlGaN, GaInN, and GaInN.
- [c9] 8. A device as recited in claim 1 further comprising a phosphor coating on said chip.
- [c10] 9. A device as recited in claim 1 further comprising a power module for powering the light source, said power module including a fitting for installation in a traditional light bulb socket and an AC/DC converter for converting AC power from traditional building wiring to DC power usable by a semiconductor devices.
- [c11] 10. A device as recited in claim 1 wherein at least one of said heat sink includes a material selected from the group consisting of include copper, aluminum, silicon carbide, boron nitride natural diamond, monocrystalline diamond, polycrystalline diamond, polycrystalline diamond compacts, diamond deposited through chemical vapor deposition and diamond deposited through physical vapor deposition.

11. A device as recited in claim 1 further comprising a quantity of heat conductive adhesive located between said chip and said primary heat sink and serving to conduct heat from said chip to said primary heat sink.

[c12]

12. A device as recited in claim 1 further comprising a quantity of light reflective adhesive located between said chip and said primary heat sink.

[c13]

13. A semiconductor light source for emitting light to illuminate a space used by humans, the semiconductor light source comprising:

an enclosure, said enclosure being fabricated from a material substantially transparent to white light,

a base to which said enclosure is mounted,

an interior volume within said enclosure,

a secondary heat sink located in said interior volume, said secondary heat sink being capable of drawing heat from one or more semiconductor devices,

a plurality of primary heat sinks mounted on said secondary heat sink, each of said primary heat sinks being smaller than said secondary heat sink,

a plurality of wells, said wells being located on said primary heat sinks and being sized to accommodate mounting of a semiconductor chip therein,

a semiconductor chip capable of emitting light mounted in one of said primary heat sink wells, said semiconductor chip being capable of emitting monochromatic light,

a quantity of adhesive serving to secure said chip to said primary heat sink,

said chip including a substrate on which epitaxial layers are grown,

a buffer layer located on said substrate, said buffer layer serving to mitigate differences in material properties between said substrate and other epitaxial layers,

a first cladding layer serving to confine electron movement within the chip, said first cladding layer being adjacent said buffer layer,

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an active layer, said active layer emitting light when electrons jump to a valance state,
a second cladding layer, said second cladding layer positioned so that said active layer
lies between cladding layers, and
a contact layer on which an electron may be mounted for powering said chip, and
a coating for converting monochromatic light emitted by said chip to white light.

[c14]

14. A device as recited in claim 13 further comprising a first and a second reflective
layers, each of said first and second reflective layers being located on opposite sides of
said active layer, said reflective layers serving to reflect light emitted by said active layer.

[c15]

15. A device as recited in claim 14 wherein said reflective layers include multiple
quantum wells.

[c16]

16. A device as recited in claim 13 wherein said substrate is selected from the group
consisting of Si, GaAs, GaN, InP, sapphire, SiC, GaSb, InAs.

[c17]

17. A device as recited in claim 13 wherein said substrate is electrically conductive.

[c18]

18. A device as recited in claim 13 wherein said substrate is electrically insulative.

[c19]

19. A device as recited in claim 13 wherein at least one of said epitaxial layers includes
a material selected from the group consisting of GaN, AlGaN, AlN, AlGaN, GaInN, and
GaInN.

[c20]

20. A device as recited in claim 13 further comprising a phosphor coating on said chip.

[c21]

21. A device as recited in claim 13 further comprising a power module for powering the
light source, said power module including a fitting for installation in a traditional light
bulb socket and an AC/DC converter for converting AC power from traditional building
wiring to DC power usable by a semiconductor devices.

[c22]

~~22. A device as recited in claim 13 wherein at least one of said heat sink includes a material selected from the group consisting of include copper, aluminum, silicon carbide, boron nitride natural diamond, monocrystalline diamond, polycrystalline diamond, polycrystalline diamond compacts, diamond deposited through chemical vapor deposition and diamond deposited through physical vapor deposition.~~

[c23]

~~23. A device as recited in claim 13 further comprising a quantity of heat conductive adhesive located between said chip and said primary heat sink and serving to conduct heat from said chip to said primary heat sink.~~

[c24]

~~24. A device as recited in claim 13 further comprising a quantity of light reflective adhesive located between said chip and said primary heat sink.~~

[c25]

~~25. A device as recited in claim 13 further comprising a cover over said chip in said well.~~

[c26]

~~26. A device as recited in claim 13 further comprising a coating over said chip in said well.~~

[c27]

~~27. A device as recited in claim 13 further comprising a transparent material located in said well and covering said chip, said transparent material being capable of converting monochromatic light emitted by said chip to white light.~~

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